

## **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions of claims in this application.

Please cancel claims 6-9 without prejudice or disclaimer, and add new claims 16-21, as follows:

1-9. (Canceled).

10. (Previously Presented) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:

placing the workpiece in a hermetically sealed process chamber;

introducing processing gas into the process chamber;

pressurizing the process chamber to a pressure equal to or higher than

500 mTorr;

etching the organic film; and

stopping the etching before the etching goes through the organic film.

11. (Previously Presented) A method of etching according to claim 10, wherein the processing gas comprises a gas comprising nitrogen atoms and a gas comprising hydrogen atoms.

12. (Previously Presented) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:

placing the workpiece in a hermetically sealed process chamber;

introducing processing gas comprising a gas comprising nitrogen atoms

and a gas comprising hydrogen atoms into the process chamber;

pressurizing the process chamber to a pressure between 500 - 800 mTorr;

etching the organic film; and

stopping the etching before the etching goes through the organic film.

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13. (Previously Presented) A method of etching according to claim 12, wherein the gas comprising nitrogen atoms constitute  $N_2$  and the gas comprising hydrogen atoms constitute  $H_2$ .
14. (Previously Presented) A method of etching according to claim 12, wherein the processing gas further comprises Ar.
15. (Previously Presented) A method of etching according to claim 13, wherein the processing gas further comprises Ar.
16. (New) A method of etching according to claim 10, wherein the method is a damascene process.
17. (New) A method of etching according to claim 10, wherein the method is applied to a dual damascene process wherein etching the organic film is etching the organic film approximately halfway through the organic film for a wiring groove.
18. (New) A method of etching according to claim 10, wherein etching the organic film etches the organic film approximately halfway through the organic film.
19. (New) A method of etching according to claim 12, wherein the method is a damascene process.
20. (New) A method of etching according to claim 12, wherein the method is applied to a dual damascene process wherein etching the organic film is etching the organic film approximately halfway through the organic film for a wiring groove.
21. (New) A method of etching according to claim 12, wherein etching the organic film etches the organic film approximately halfway through the organic film.

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